

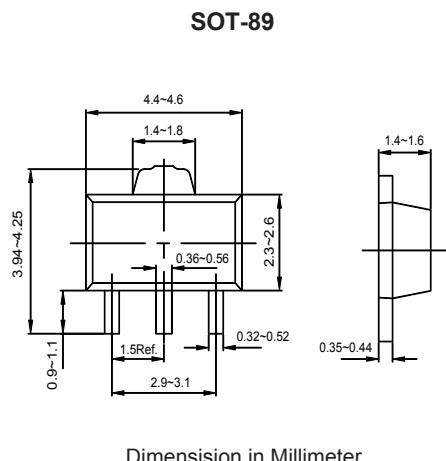
RoHS Compliant Product



- 1.BASE
- 2.COLLECTOR
- 3.EMITTER

Features

Power dissipation
 P_{CM} : 0.5 W ($T_{amb}=25^{\circ}C$)
 Collector current
 I_{CM} : 1 A
 Collector-base voltage
 $V_{(BR)CBO}$: 60 V



Dimension in Millimeter

Operating and storage junction temperature range

T_J, T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$

ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=100\mu A, I_E=0$	60		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=10mA, I_B=0$	60		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=10\mu A, I_C=0$	5		V
Collector cut-off current	I_{CBO}	$V_{CB}=30V, I_E=0$		0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=5V, I_C=0$		0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE}=2V, I_C=150mA$	63	250	
			63	160	
			100	250	
	$h_{FE(2)}$	$V_{CE}=2V, I_C=5mA$	40		
	$h_{FE(3)}$	$V_{CE}=2V, I_C=500mA$	25		
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=500mA, I_B=50mA$		0.5	V
Base-emitter voltage	$V_{BE(ON)}$	$I_C=500mA, V_{CE}=2V$		1	V
Transition frequency	f_T	$V_{CE}=10V, I_C=50mA$ $f=100MHz$	130		MHz

DEVICE MARKING	BCX55=BE BCX55-10=BG BCX55-16=BM
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